

L Number	Hits	Search Text	DB	Time stamp
23	171	p-type adj polysilicon near4 gate	USPAT; US-PGPUB	2002/04/06 13:46
24	279	p-type adj polysilicon same gate	USPAT; US-PGPUB	2002/04/06 13:46
25	108	(p-type adj polysilicon same gate) not (p-type adj polysilicon near4 gate)	USPAT; US-PGPUB	2002/04/06 13:46
26	67	p-type adj polysilicon near4 gate	EPO; JPO; DERWENT; IBM_TDB	2002/04/06 15:46
27	11	YAMAGUCHI.in. and SHUSAKU.in.	USPAT; US-PGPUB	2002/04/06 15:21
28	71800	YAMAGUCHI.in. SHUSAKU.in.	EPO; JPO; DERWENT; IBM_TDB	2002/04/06 15:21
29	0	jp-09036318-\$.did.	USPAT; US-PGPUB	2002/04/06 15:22
-	53807	drain near2 source	USPAT; US-PGPUB	2002/04/05 15:04
-	1033	(drain near2 source) near2 ground	USPAT; US-PGPUB	2002/04/05 15:04
-	851	((drain near2 source) near2 ground) same gate	USPAT; US-PGPUB	2002/04/05 15:04
-	186	((drain near2 source) near2 ground) same (gate near2 (supply voltage))	USPAT; US-PGPUB	2002/04/05 15:21
-	174	capacitor adj connected adj transistor	USPAT; US-PGPUB	2002/04/05 15:21
-	19	(capacitor adj connected adj transistor) same ground	USPAT; US-PGPUB	2002/04/05 16:32
-	17	7.clm.	USPAT; US-PGPUB	2002/04/05 16:33
-	171	p-type adj polysilicon near4 gate	USPAT; US-PGPUB	2002/04/06 14:19
-	1	("6000843").PN.	USPAT; US-PGPUB	2002/04/05 17:04